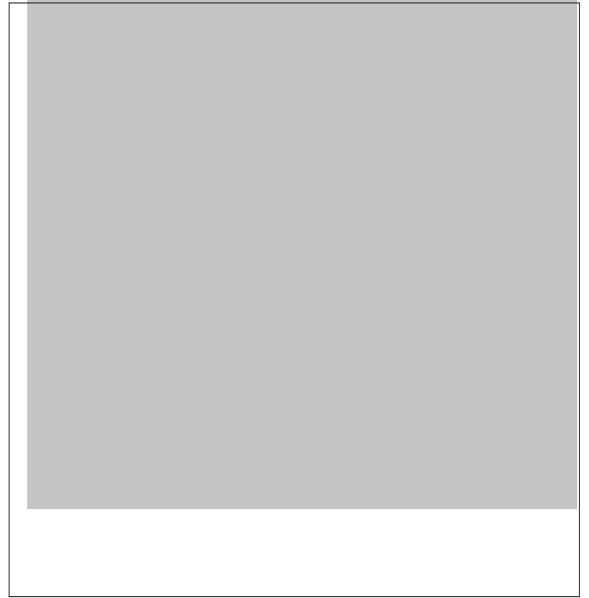


HC! 'D`UghjW!9bWUdg i`UhY`ACG : 9HG

ÁŠ[ , ÁÜÖÙÇ[ ]DÁÁ  
Š[ , ^!ÁÖæ ]æ&æcæ }&^•Á  
ÁŠ[ , ^!ÁVÁ [cæ]ÁÖæc^ÁÖ@æ! \*^Á  
Vá\* @c^!ÁXÜÖÁÙ ]^&á-á&æcá [ ]•Á  
ÁÆçæ]æ }&@^ÁÖ }^! \*^ÁÙ ]^&á-á^áÁ  
Í€XÁPÈÖ@æ }^!Á T U Ò Ø V



A5L=A I A`F5H=B ; G`5B8`7<5F57H9F=GH=7G

O GÍ »Ô Æ { àâ^ }c V^ { ]^!æç~ !^ Ç~ }|^••



F5H-B ; G 5B8 7<5F57H9F=GH=7 7 I FJ9G

ACG: 9H`9@97HF=75@`7<5F57H9F=GH=7G`V\_GM G I C A } | ^ . . A [ c @ ^ ! , i . ^ A . ] ^ & i - i ^ a

DUfU a YhYf	Gm a Vc`	HYgh`7cbX]h]cb	A]b	Hmd	AUI	I b]hg
Gate-Body Leakage Current (note 4)	I <sub>GSS</sub>	V <sub>DS</sub> =0V, V <sub>GS</sub> =±30V			±100	nA
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> = 0V, I <sub>D</sub> =250μA	600			V
Gate-Threshold Voltage	V <sub>GS(th)</sub>		2.0		4.0	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =600V, V <sub>GS</sub> =0V			1	μA
Forward transconductance	g <sub>fs</sub>	V <sub>DS</sub> = 0V, I <sub>D</sub> =2 A				S
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =2.25A			2.5	Ω
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =25V, V <sub>GS</sub> =0V, f =1MHz			670	pF
Output Capacitance	C <sub>oss</sub>				72	
Reverse Transfer Capacitance	C <sub>rss</sub>				8.5	
Turn-On Delay Time (note 4)	t <sub>d(on)</sub>	V <sub>DD</sub> =300V, I <sub>D</sub> =4.5 A, R <sub>G</sub> =25			30	ns
Rise Time (note 4)	t <sub>r</sub>				90	
Turn-Off Delay Time (note 4)	t <sub>d(off)</sub>				85	
Fall Time (note 4)	t <sub>f</sub>				100	
Forward on Voltage (note 4)	V <sub>SD</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =4.5A			1.4	V

BchYg.`

1. E<sub>AS</sub> condition: T<sub>j</sub>=25 , V<sub>DD</sub>=50V, R<sub>G</sub>=25 , L=16mH, I<sub>AS</sub>=5A
2. This test is performed with no heat sink at T<sub>a</sub>=25 .
3. This test is performed with infinite heat sink at T<sub>c</sub>=25 .
4. Pulse Test : Pulse Widthm300μs, Duty Cycle m2%.